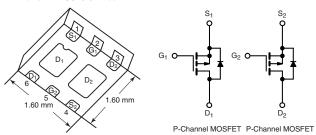


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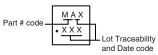
# **Dual P-Channel 20 V (D-S) MOSFET**

PRODUCT SUMMARY	
V <sub>DS</sub> (V)	- 20
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS}$ = - 4.5 V	0.295
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS}$ = - 2.5 V	0.420
$R_{DS(on)}(\Omega)$ at $V_{GS} = -1.8 \text{ V}$	0.560
I <sub>D</sub> (A) <sup>f</sup>	- 2.6
Configuration	Dual

#### PowerPAK SC75-6L-Dual



#### Marking Code



#### **FEATURES**

 High Quality Manufacturing Process Using SMM Process Flow



 Halogen-free According to IEC 61249-2-21 Definition

ROHS COMPLIANT HALOGEN FREE

- TrenchFET® Power MOSFET
- New Thermally Enhanced PowerPAK® SC-75 Package
  - Small Footprint Area
- Compliant to RoHS Directive 2002/95/EC
- Find out more about Vishay's Medical Products at: www.vishay.com/medical-mosfets

#### **APPLICATION EXAMPLES**

- Medical Implantable Applications Including
  - Drug Delivery Systems
  - Defibrillators
  - Pacemakers
  - Hearing Aids
  - Other Implantable Devices
- Load Switch, PA Switch and Battery Switch for Portable Devices

ORDERING INFORMATION						
Package	PowerPAK SC-75					
Lead (Pb)-free and Halogen-free	SMMB911DK-T1-GE3					

PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		$V_{DS}$	- 20	V	
Gate-Source Voltage		V <sub>GS</sub>	± 8		
	T <sub>C</sub> = 25 °C		- 2.6		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 70 °C		- 2.1		
	T <sub>A</sub> = 25 °C <sup>a, b</sup>	I <sub>D</sub>	- 1.5		
	T <sub>A</sub> = 70 °Ca, b		- 1.2	A	
Pulsed Drain Current		I <sub>DM</sub>	- 5		
Continuous Course Drain Diada Current	T <sub>C</sub> = 25 °C	1	- 2.6		
Continuous Source-Drain Diode Current	T <sub>A</sub> = 25 °C <sup>a, b</sup>	I <sub>S</sub>	- 0.9		
	T <sub>C</sub> = 25 °C		3.1	w	
Maximum Daylar Dissination	T <sub>C</sub> = 70 °C	D	2		
Maximum Power Dissipation	T <sub>A</sub> = 25 °Ca, b	$P_{D}$	1.1		
	T <sub>A</sub> = 70 °C <sup>a, b</sup>		0.7		
Operating Junction and Storage Temperature Ra	nge	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 150	°C	
Soldering Recommendations (Peak Temperature	)c, d	-	260	°C	

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THERMAL RESISTANCE RATINGS									
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT				
Junction-to-Ambient <sup>a, e</sup>	t ≤ 5 s	R <sub>thJA</sub>	R <sub>thJA</sub> 90 115 °C/W						
Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	32	40	C/VV				

#### **Notes**

- a. Surface mounted on 1" x 1" FR4 board.
- b. t = 5 s.
- c. See Solder Profile (<a href="https://www.vishay.com/ppg?73257">www.vishay.com/ppg?73257</a>). The PowerPAK SC-75 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- d. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- e. Maximum under steady state conditions is 125 °C/W.
- f. Based on  $T_C = 25$  °C.

<b>SPECIFICATIONS</b> $T_J = 25  ^{\circ}C$ ,	unless other	wise noted					
PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT	
Static					•	•	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		- 20	-	-	V
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$		_ 250 uA	-	- 19	-	m\//°C
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	]	<sub>D</sub> = - 250 μA	-	1.9	-	mV/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = - 250 μA	- 0.4	-	- 1	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	= 0 V, V <sub>GS</sub> = ± 8 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 20 V	1	-	- 1	μΑ
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS} = -20 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$	-	-	- 10	μΑ
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	V <sub>GS</sub> = - 4.5 V	$V_{DS} \le 5 V$	5	-	-	Α
		V <sub>GS</sub> = - 4.5 V	I <sub>D</sub> = - 1.5 A	-	0.242	0.295	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 2.5 V	I <sub>D</sub> = - 1.2 A	-	0.345	0.420	Ω
		V <sub>GS</sub> = - 1.8 V	I <sub>D</sub> = - 0.18 A	-	0.455	0.560	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> =	- 10 V, I <sub>D</sub> = - 1.5 A	-	3	-	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>		V <sub>DS</sub> = - 10 V, f = 1 MHz	-	115	-	pF
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	30	-	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	20	-	
Total Cata Charge		V <sub>GS</sub> = - 8 V	$V_{DS} = -10 \text{ V}, I_{D} = -1.7 \text{ A}$	-	2.6	4.0	nC
Total Gate Charge	$Q_g$			-	1.6	2.5	
Gate-Source Charge	Q <sub>gs</sub>	V <sub>GS</sub> = - 4.5 V	$V_{DS} = -10 \text{ V}, I_{D} = -1.7 \text{ A}$	-	0.3	-	
Gate-Drain Charge	$Q_{gd}$			-	0.5	-	
Gate Resistance	$R_g$		f = 1 MHz	-	7	-	Ω
Turn-On Delay Time	t <sub>d(on)</sub>			-	12	20	
Rise Time	t <sub>r</sub>	$V_{DD} = -10 \text{ V}, R_L = 7.1 \Omega$ $I_D \cong -1.4 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$		-	45	70	
Turn-Off Delay Time	t <sub>d(off)</sub>			-	10	15	
Fall Time	t <sub>f</sub>			-	31	50	
Turn-On Delay Time	t <sub>d(on)</sub>			-	3	10	ns
Rise Time	t <sub>r</sub>	$V_{DD} = -10 \text{ V}, R_L = 7.1 \Omega$		-	25	40	
Turn-Off Delay Time	t <sub>d(off)</sub>	I <sub>D</sub> ≅ - 1.4 A	-	10	15		
Fall Time	t <sub>f</sub>			-	10	15	
Source-Drain Body Diode Characteristic	s						
Continuous Source-Drain Diode Current	I <sub>S</sub>		T <sub>C</sub> = 25 °C	-	-	- 2.6	
Pulse Diode Forward Current	I <sub>SM</sub>			-	-	5	A





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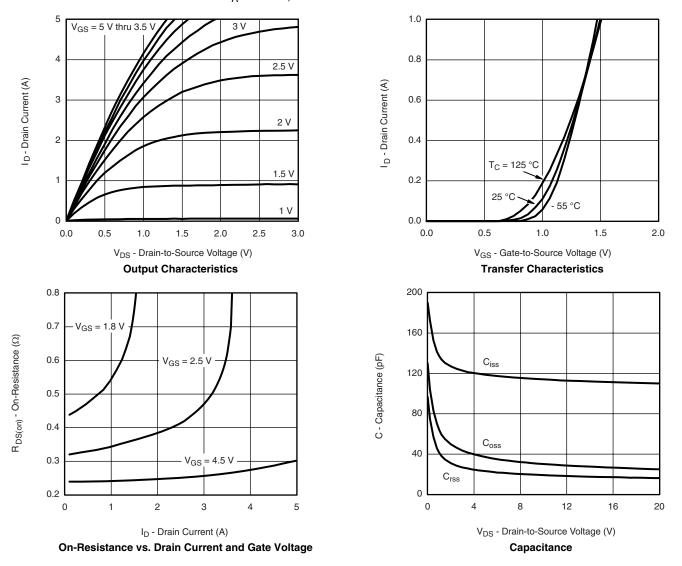
<b>SPECIFICATIONS</b> T <sub>J</sub> = 25 °C, unless otherwise noted										
PARAMETER SYMBOL TEST CONDITIONS MIN. TYP. MAX.										
Source-Drain Body Diode Characteristics										
Body Diode Voltage $V_{SD}$ $I_S = -1.4 \text{ A}, V_{GS} = 0 \text{ V}$ - $-0.8 -1.2$										
Body Diode Reverse Recovery Time	t <sub>rr</sub>		-	25	50	ns				
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	l <sub>F</sub> = - 1.4 A, dl/dt = 100 A/μs, T <sub>J</sub> = 25 °C	-	26	50	nC				
Reverse Recovery Fall Time	t <sub>a</sub>	$1 = -1.4 \text{ A}, \text{ di/dt} = 100 \text{ A/} \mu \text{s}, \text{ 1} = 25 \text{ C}$	-	19	-	no				
Reverse Recovery Rise Time	t <sub>b</sub>		-	6	-	ns				

#### **Notes**

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

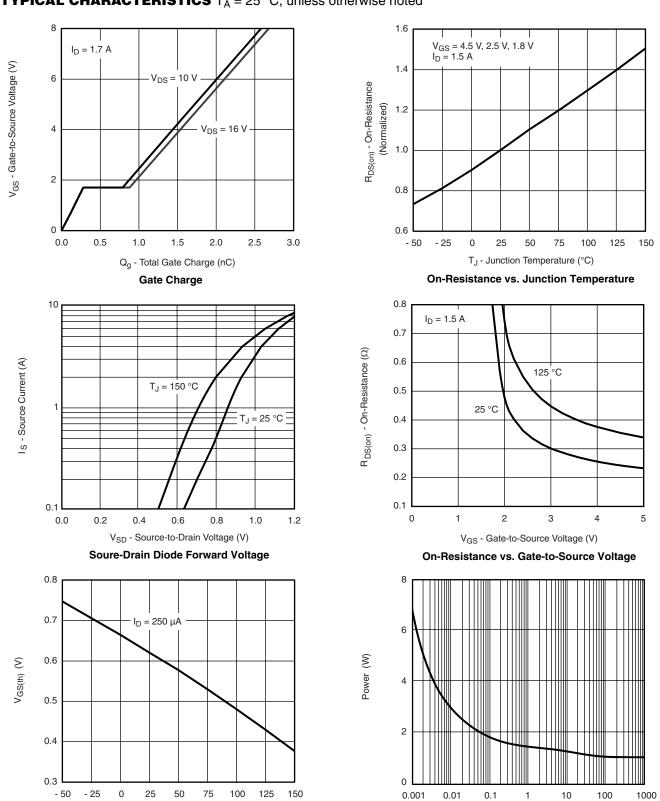
## TYPICAL CHARACTERISTICS T<sub>A</sub> = 25 °C, unless otherwise noted



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## **TYPICAL CHARACTERISTICS** $T_A = 25$ °C, unless otherwise noted



 $T_J$  - Temperature (°C)

**Threshold Voltage** 

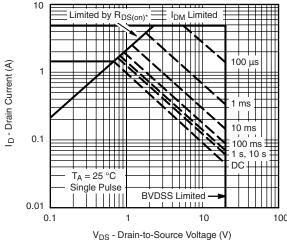
Time (s)

Single Pulse Power, Junction-to-Ambient



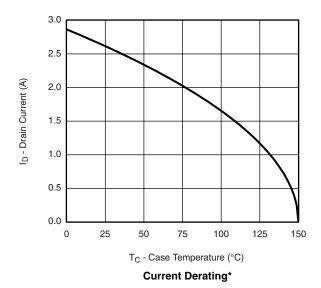
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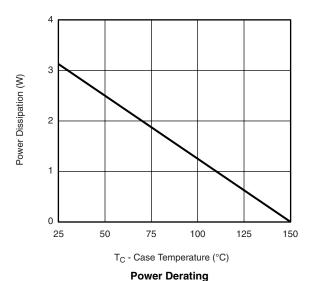
### TYPICAL CHARACTERISTICS T<sub>A</sub> = 25 °C, unless otherwise noted



\* V<sub>GS</sub> > minimum V<sub>GS</sub> at which R<sub>DS(on)</sub> is specified

#### Safe Operating Area, Junction-to-Ambient



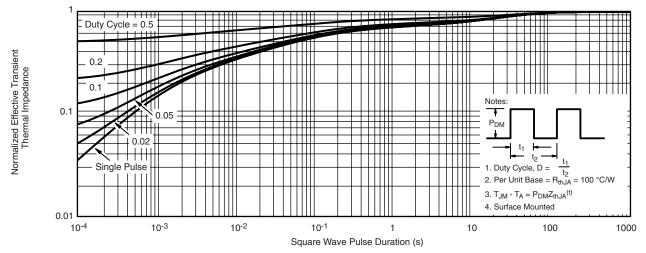


<sup>\*</sup> The power dissipation  $P_D$  is based on  $T_{J(max.)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

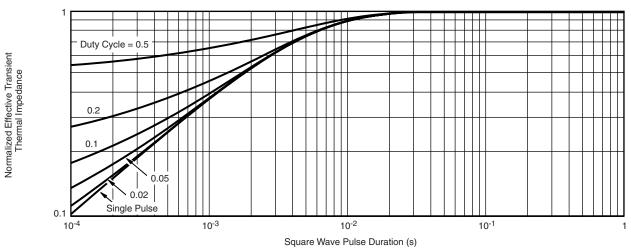
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### TYPICAL CHARACTERISTICS T<sub>A</sub> = 25 °C, unless otherwise noted



#### Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

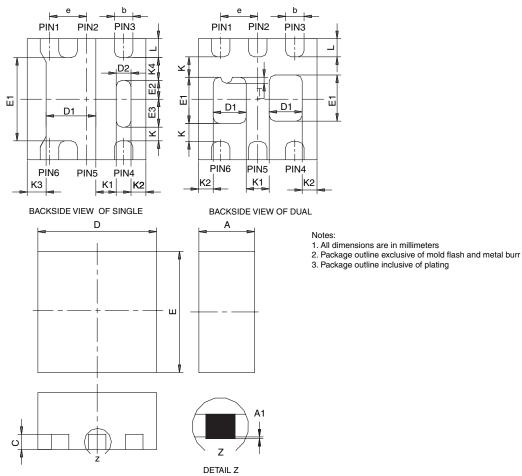
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?65174">www.vishay.com/ppg?65174</a>.

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## PowerPAK® SC75-6L



	SINGLE PAD					DUAL PAD						
DIM	M	ILLIMETER	RS		INCHES		M	MILLIMETERS			INCHES	
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.18	0.25	0.33	0.007	0.010	0.013	0.18	0.25	0.33	0.007	0.010	0.013
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067
D1	0.57	0.67	0.77	0.022	0.026	0.030	0.34	0.44	0.54	0.013	0.017	0.021
D2	0.10	0.20	0.30	0.004	0.008	0.012						
Е	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067
E1	1.00	1.10	1.20	0.039	0.043	0.047	0.51	0.61	0.71	0.020	0.024	0.028
E2	0.20	0.25	0.30	0.008	0.010	0.012						
E3	0.32	0.37	0.42	0.013	0.015	0.017						
е		0.50 BSC			0.020 BSC	;	0.50 BSC			0.020 BSC		
K		0.180 TYP	)		0.007 TYP	ı	0.245 TYP			0.010 TYP		
K1		0.275 TYP	)		0.011 TYP	ı	0.320 TYP			0.013 TYP		
K2		0.200 TYP			0.008 TYP	ı		0.200 BSC	;		0.008 TYP	
К3		0.255 TYP	)	0.010 TYP								
K4		0.300 TYP	TYP 0.012 TYP		0.012 TYP							
L	0.15	0.25	0.35	0.006	0.010	0.014	0.15	0.25	0.35	0.006	0.010	0.014
Т							0.03	0.08	0.13	0.001	0.003	0.005
ECN: C	N: C07431 Rev C 06-Aug-07											

ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5935

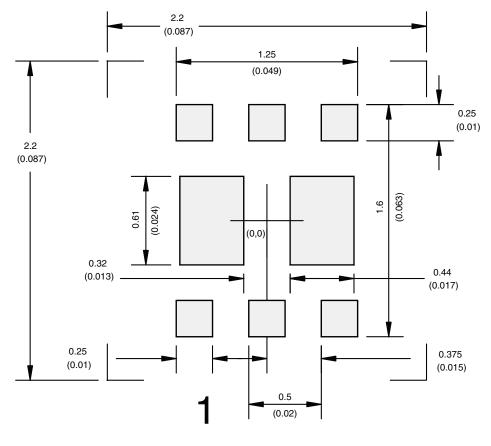
Document Number: 73000

06-Aug-07

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### RECOMMENDED PAD LAYOUT FOR PowerPAK® SC75-6L Dual



Dimensions in mm/(Inches)

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Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

Revision: 02-Oct-12 Document Number: 91000